

MSB92WT1G, MSB92AWT1G

PNP Silicon General Purpose High Voltage Transistor

This PNP Silicon Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-300	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	-300	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	500	mAdc
Electrostatic Discharge	ESD	MM > 16,000, MM > 2,000	V

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P _D	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

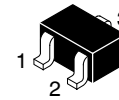
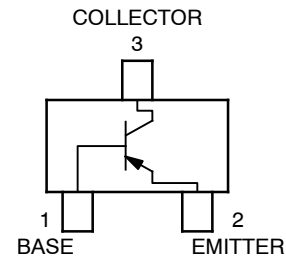
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



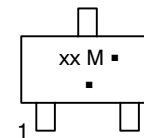
ON Semiconductor®

<http://onsemi.com>



SC-70 (SOT-323)
CASE 419
STYLE 3

MARKING DIAGRAM



- xx = Device Code
x = 2D or D2
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MSB92WT1G	SC-70/ SOT-323 (Pb-Free)	3000/Tape & Reel
MSB92AWT1G	SC-70/ SOT-323 (Pb-Free)	3000/Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage ($I_C = -1.0$ mA dc, $I_B = 0$)	$V_{(BR)CEO}$	-300	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -100$ μ A dc, $I_E = 0$)	$V_{(BR)CBO}$	-300	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -100$ μ A dc, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = -200$ Vdc, $I_E = 0$)	I_{CBO}	-	-0.25	μ A
Emitter-Base Cutoff Current ($V_{EB} = -3.0$ Vdc, $I_B = 0$)	I_{EBO}	-	-0.1	μ A
DC Current Gain (Note 2) MSB92WT1: ($V_{CE} = -10$ Vdc, $I_C = -1.0$ mA dc) MSB92AWT1: ($V_{CE} = -10$ Vdc, $I_C = -1.0$ mA dc) ($V_{CE} = -10$ Vdc, $I_C = -10$ mA dc) ($V_{CE} = -10$ Vdc, $I_C = -30$ mA dc)	h_{FE1} h_{FE1} h_{FE2} h_{FE3}	25 120 40 25	- 200 - -	-
Collector-Emitter Saturation Voltage (Note 2) ($I_C = -20$ mA dc, $I_B = -2.0$ mA dc)	$V_{CE(sat)}$	-	-0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = -20$ mA dc, $I_B = -2.0$ mA dc)	$V_{BE(sat)}$	-	-0.9	Vdc

SMALL SIGNAL CHARACTERISTICS

Current - Gain - Bandwidth Product ($I_C = -10$ mA dc, $V_{CE} = -20$ Vdc, $f = 20$ MHz)	f_T	50	-	MHz
Collector-Base Capacitance ($V_{CB} = -20$ Vdc, $I_E = 0$, $f = 1.0$ MHz)	C_{cb}	-	6.0	pF

2. Pulse Test: Pulse Width ≤ 300 μ s, D.C. $\leq 2\%$.

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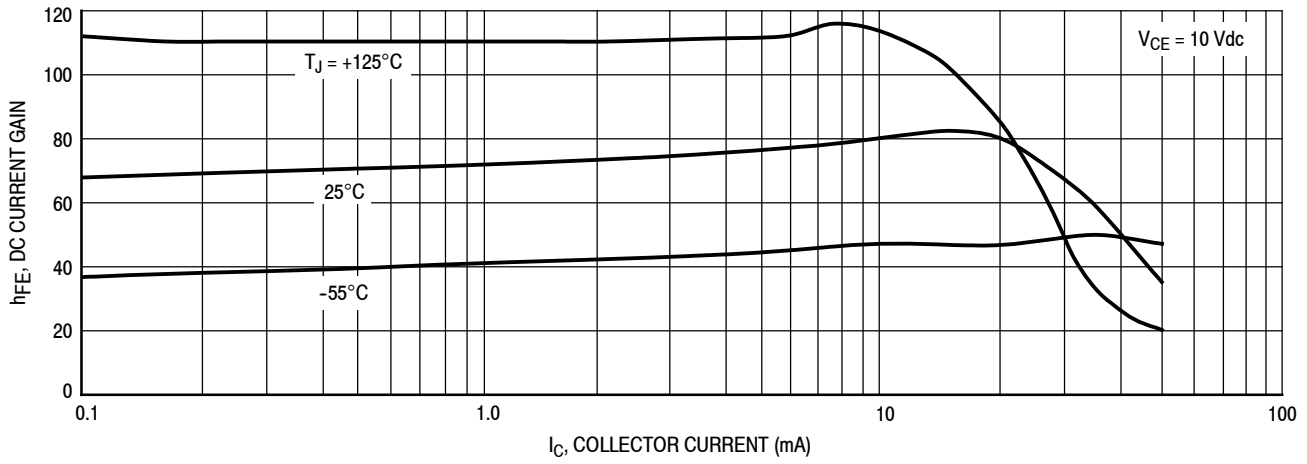


Figure 1. DC Current Gain

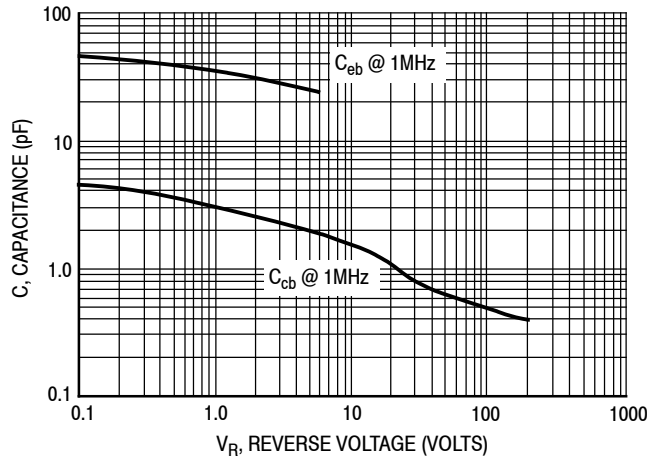


Figure 2. Capacitance

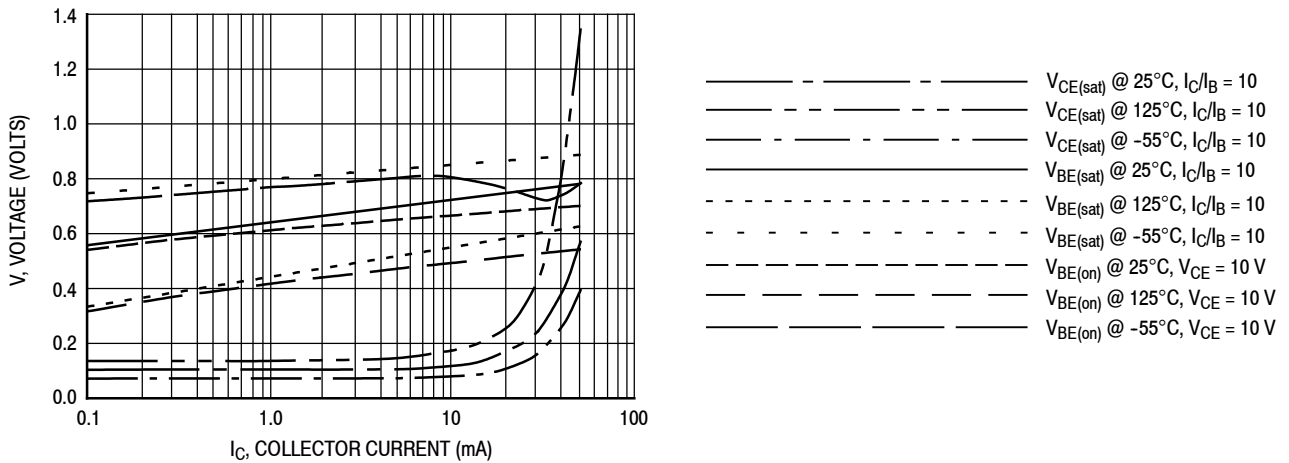


Figure 3. "ON" Voltages

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|-------------------------------------------------------|-------------------------------------------------------|-------------------------------------------------------|------------------------------------------------------------|-------------------------------------------------------------|---------------------------------------------------------|
| STYLE 1:
CANCELLED | STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE | STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE | |
| STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE | STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE |

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